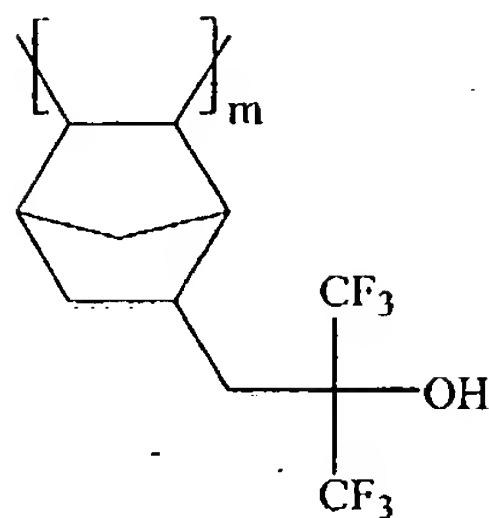


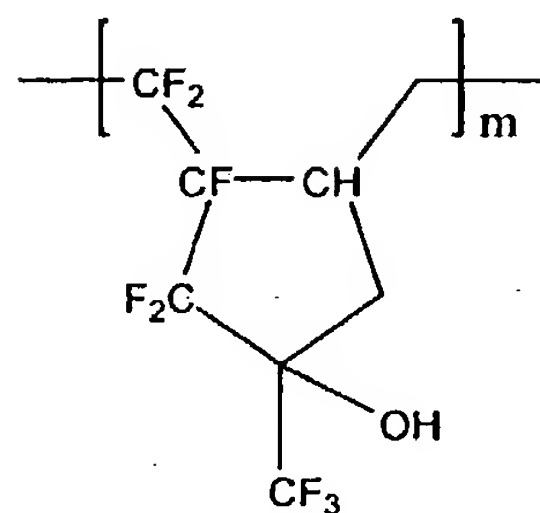
What is Claimed is:

1. A light absorption depressant comprising:
5 a TIMD (tetraisopropyl methylene diphosphonate) which depresses light absorption at a wavelength of less than 200nm.
2. The light absorption depressant according to claim 1, wherein the
wavelength is 157 nm or 193 nm.
10
3. A photoresist composition comprising a TIMD (tetraisopropyl
methylene diphosphonate).
4. The photoresist composition according to claim 3 further comprising
15 a base resin and wherein the TIMD is present in an amount ranging from 0.01 to 25 wt% based on the base resin.
5. The photoresist composition according to claim 4, wherein the TIMD
is present in an amount ranging from 0.01 to 20 wt% based on the base resin.
20
6. The photoresist composition according to claim 3, wherein the TIMD
is added in the photoresist composition for a 157 nm light source or for a 193 nm light
source.
- 25 7. The photoresist composition according to claim 3, which comprises
(1) a poly(norbornenehexafluoroalcohol) represented by Formula 2 or (2) a blend
polymer of polymers represented by Formula 3a and Formula 3b as a base resin.

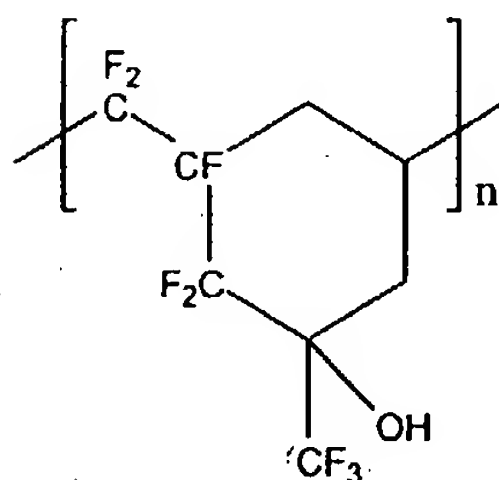
Formula 2



Formula 3a



Formula 3b



8. The photoresist composition according to claim 7, wherein the composition is a chemically amplified photoresist composition comprising a photoacid generator.

9. A process for forming a photoresist pattern, comprising:

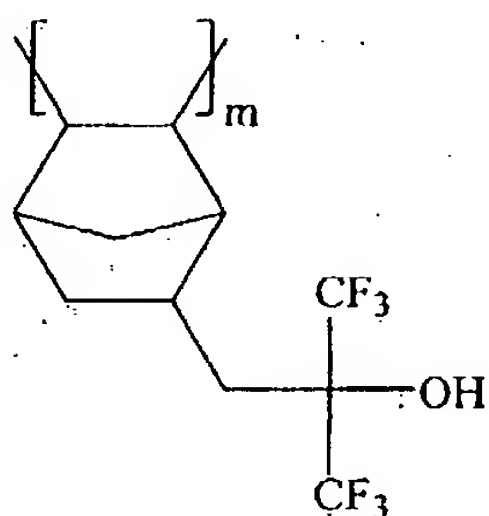
- (a) coating the photoresist composition of claim 3 on an underlying layer to form a photoresist film;
- (b) baking the photoresist film, and then exposing the baked photoresist film to light;
- (c) baking the exposed photoresist film; and
- (d) developing the baked photoresist film to obtain a photoresist pattern.

10. A semiconductor device manufactured according to the process of claim 9.

11. A photoresist composition comprising a hydrocarbon compound
5 including P=O groups.

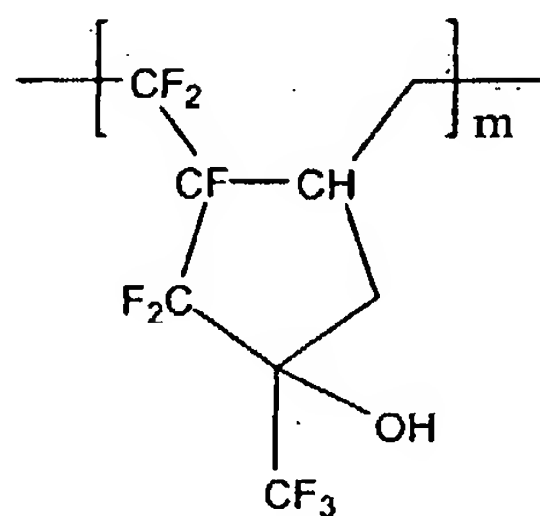
12. A photoresist composition comprising a TIMD (tetraisopropyl methylene diphosphonate) and a base resin selected from the group consisting of

Formula 2

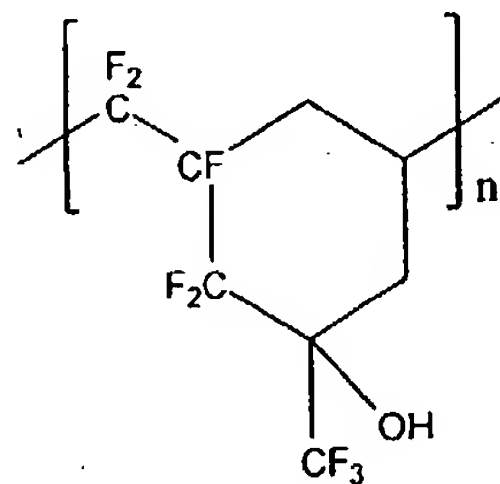


10

Formula 3a



Formula 3b



and mixtures thereof.

5

13. The photoresist composition according to claim 12, wherein the TIMD is present in an amount ranging from 0.01 to 25 wt% based on the base resin.

14. The photoresist composition according to claim 13, wherein the
10 TIMD is present in an amount ranging from 0.01 to 20 wt% based on the base resin.

15. The photoresist composition according to claim 12, wherein the TIMD is added in the photoresist composition for a 157 nm light source or for a 193 nm light source.

15

16. The photoresist composition according to claim 15, wherein the composition is a chemically amplified photoresist composition comprising a photoacid generator.

20

17. A process for forming a photoresist pattern, comprising:

- (a) coating the photoresist composition of claim 12 on an underlying layer to form a photoresist film;
- (b) baking the photoresist film, and then exposing the baked photoresist film to light;
- (c) baking the exposed photoresist film; and
- (d) developing the baked photoresist film to obtain a photoresist pattern.

25

18. The photoresist composition according to claim 12 further comprising a hydrocarbon compound including P=O groups.

19. A semiconductor device manufactured according to the process of claim 17.